



No.3763

2SJ190

P-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

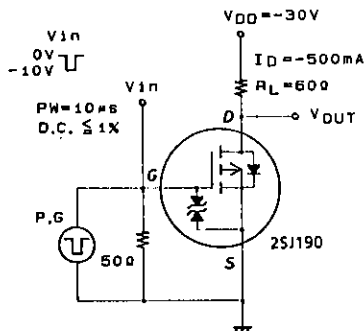
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V _{DSS}	-60	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current (DC)	I _D	-1	A
Drain Current (Pulse)	I _{DP}	-4	A
Allowable Power Dissipation	P _D	PW ≤ 10 μs, duty cycle ≤ 1%	3.5
		(T _c = 25°C Mounted on ceramic board (250mm ² × 0.8mm))	1.5
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

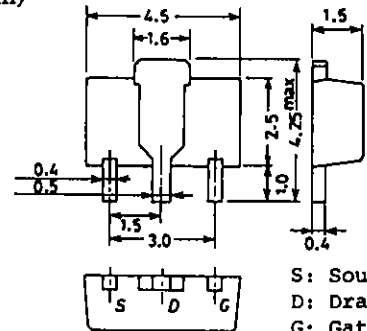
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DSS} = -60V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -500mA	0.6	1.0		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = -500mA, V _{GS} = -10V		0.9	1.2	Ω
	R _{DS(on)}	I _D = -500mA, V _{GS} = -4V		1.2	1.6	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		160		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		60		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		10		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	"		13		ns
Turn-OFF Delay Time	t _{d(off)}	"		70		ns
Fall Time	t _f	"		30		ns
Diode Forward Voltage	V _{SD}	I _S = -1A, V _{GS} = 0		-0.9		V

Switching Time Test Circuit



Package Dimensions 2062

(unit: mm)

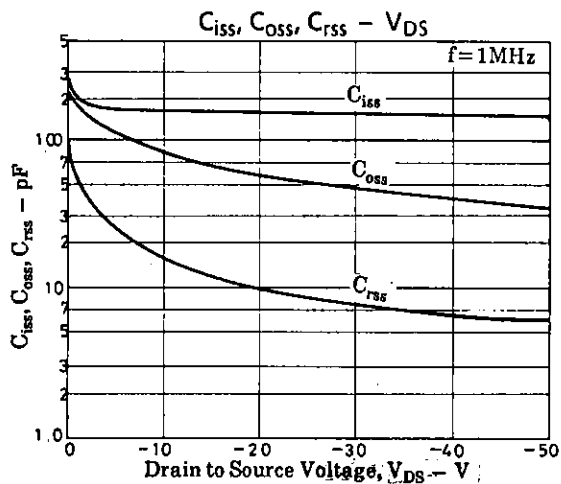
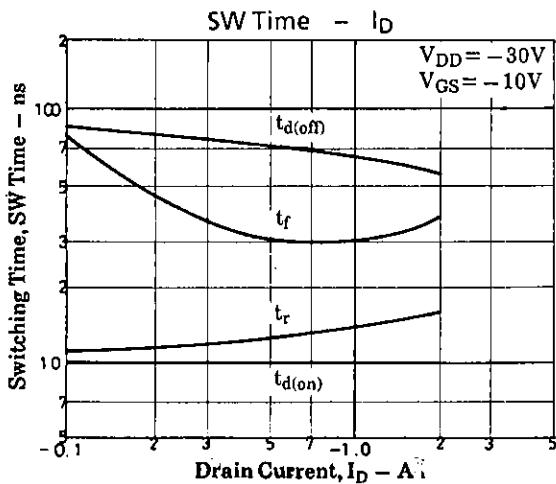
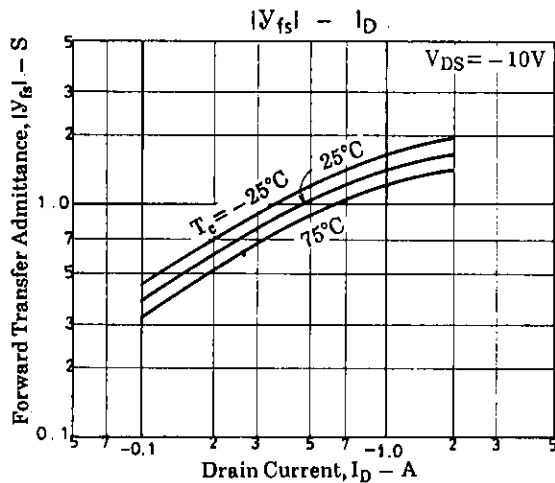
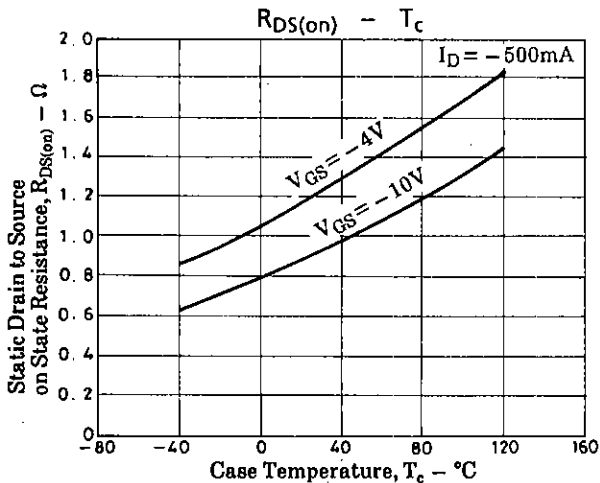
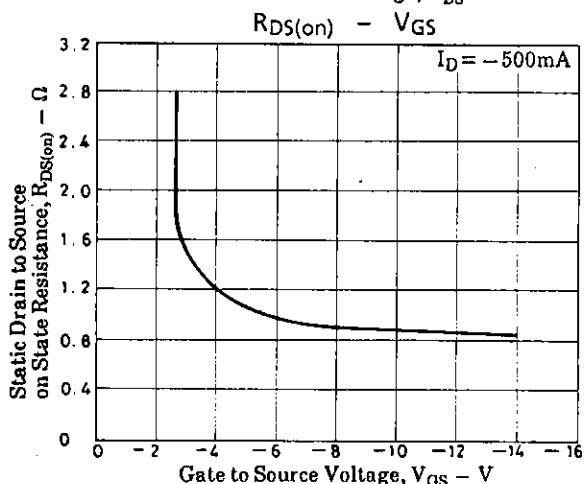
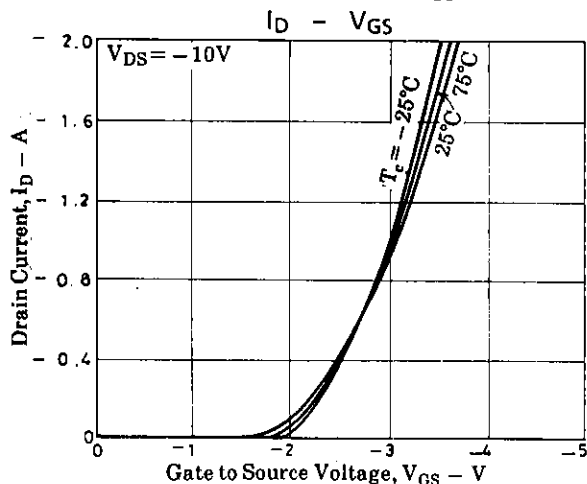
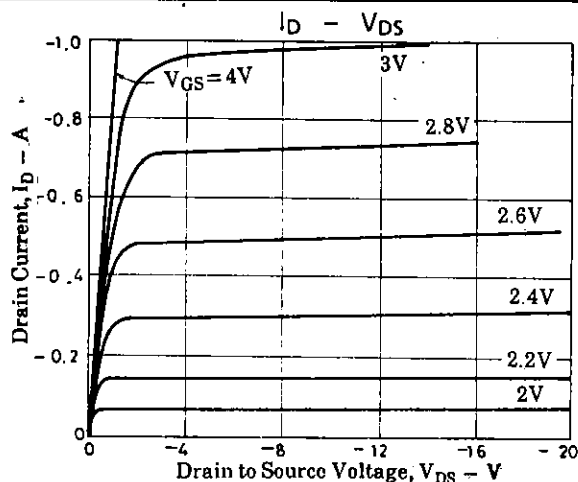
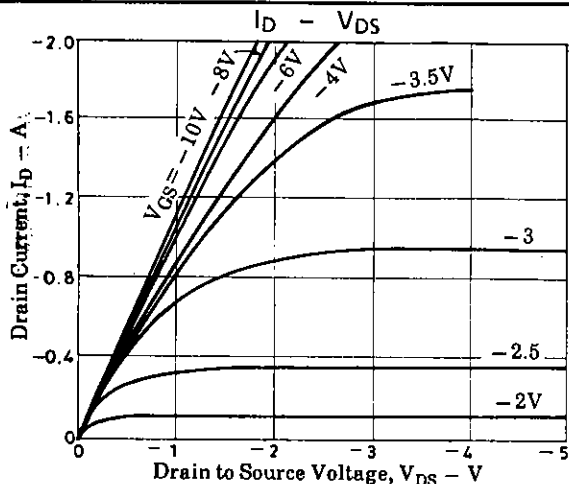


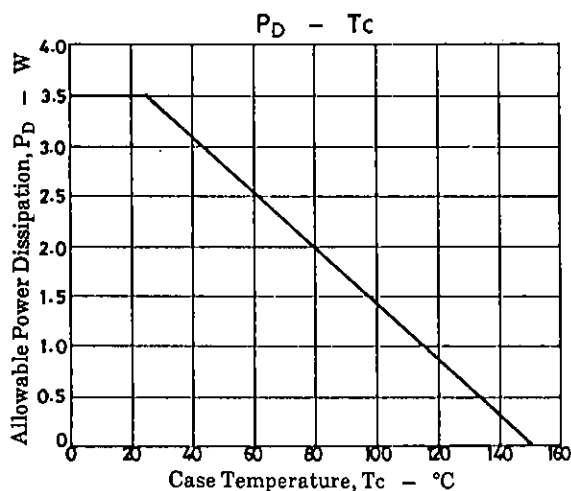
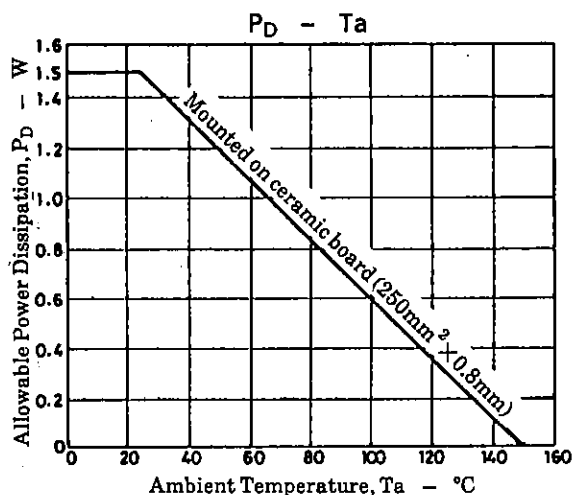
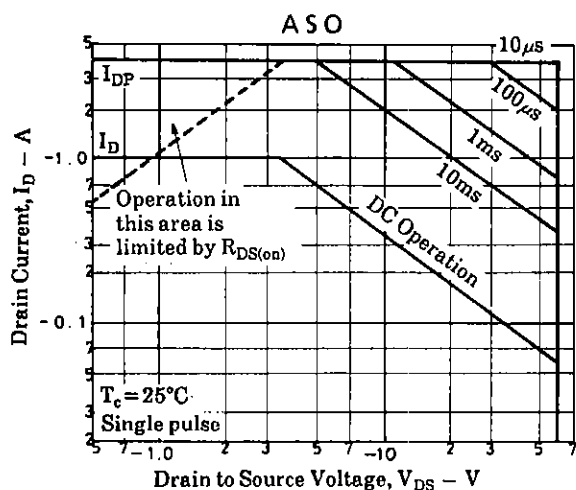
S: Source
D: Drain
G: Gate

SANYO: PCP

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